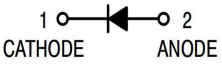
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BAS21HT1G
High Voltage Switching Diode

- These are Pb−Free Devices

HIGH VOLTAGE SWITCHING DIODE



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Continuous Reverse Voltage	V_R	250	Vdc
Repetitive Peak Reverse Voltage	V_{RRM}	250	Vdc
Peak Forward Current	I_F	200	mAdc
Repetitive Peak Forward Current	I_{FRM}	500	mA
Non−Repetitive Peak Forward Surge Current, 60 Hz	$I_{FSM(surge)}$	625	mAdc
Non−Repetitive Peak Forward Current (Square Wave, T_J = 25°C prior to surge) t = 1 μs t = 10 μs t = 100 μs t = 1 ms t = 1 s	I_{FSM}	 20 20 10 4 1	A

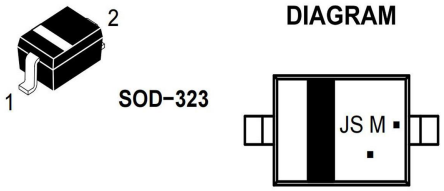
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR−5 Board, (Note 1) T_A = 25°C Derate above 25°C	P_D	200 1.57	mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	635	°C/W
Junction and Storage Temperature Range	T_J, T_{stg}	−55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR−5 Minimum Pad

MARKING DIAGRAM



JS = Device Code
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending up-
on manufacturing location.

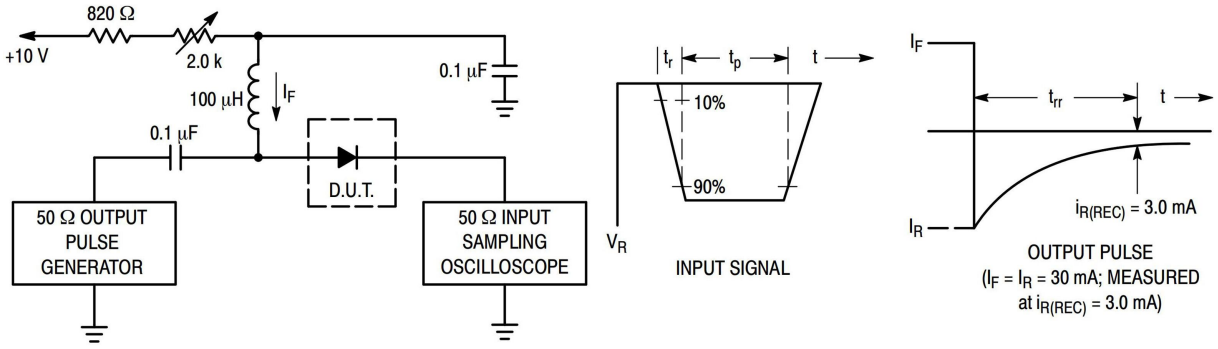
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ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Reverse Voltage Leakage Current (V_R = 200 Vdc) (V_R = 200 Vdc, T_J = 150°C)	I_R	 – –	 0.1 100	μAdc
Reverse Breakdown Voltage (I_{BR} = 100 μAdc)	$V_{(BR)}$	250	–	Vdc
Forward Voltage (I_F = 100 mAdc) (I_F = 200 mAdc)	V_F	 – –	 1000 1250	mV
Diode Capacitance (V_R = 0, f = 1.0 MHz)	C_D	–	5.0	pF
Reverse Recovery Time (I_F = I_R = 30 mAdc, R_L = 100 Ω)	t_{rr}	–	50	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.



Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 30 mA.
2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 30 mA.
3. $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

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TYPICAL CHARACTERISTICS

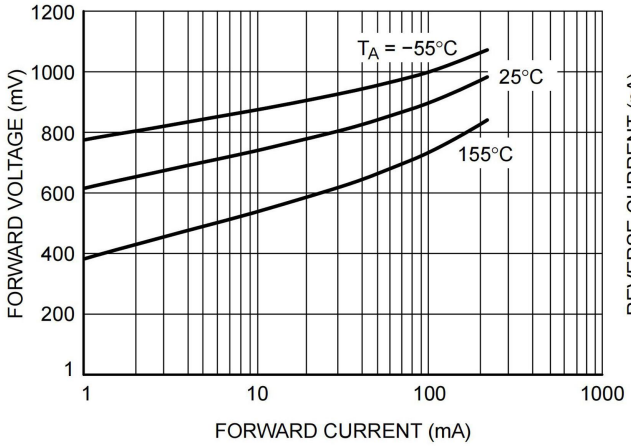


Figure 2. Forward Voltage

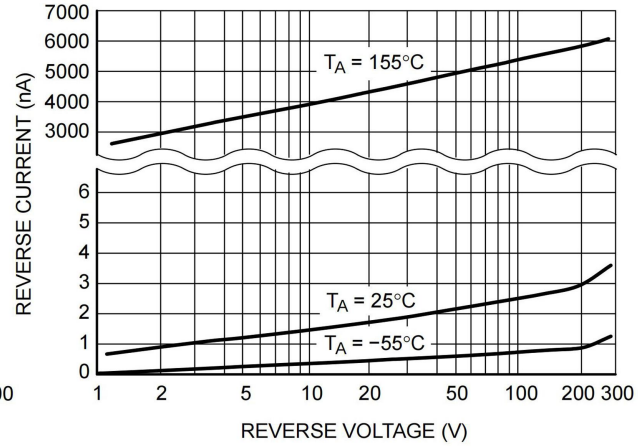


Figure 3. Reverse Leakage

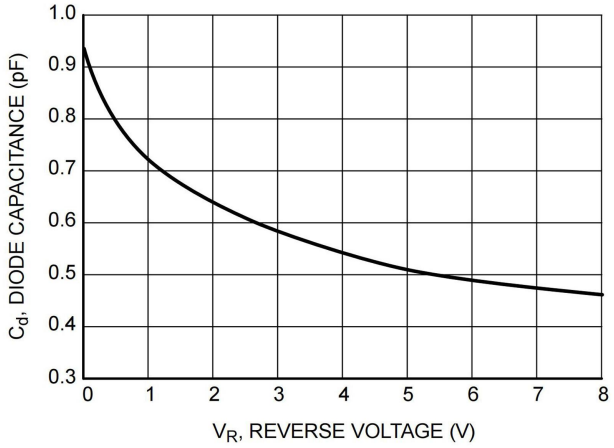


Figure 4. Diode Capacitance

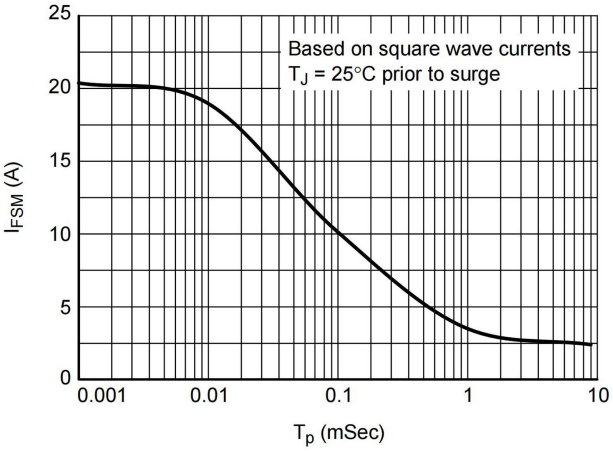


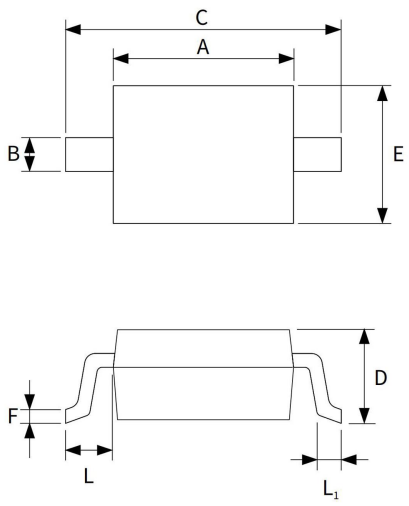
Figure 5. Maximum Non−repetitive Peak Forward Current as a Function of Pulse Duration, Typical Values

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Ordering Information

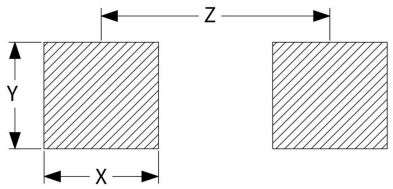
PACKAGE	PACKAGE CODE	UNIT WEIGHT(g)	REEL(pcs)	BOX(pcs)	CARTON(pcs)	DELIVERY MODE
SOD-323	R1	0.0048	3000	30000	240000	7''

Package Outline Dimensions (SOD-323)



Symbol	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	1.60	1.80	0.063	0.071
B	0.25	0.40	0.010	0.016
C	2.30	2.80	0.091	0.110
D	0.80	1.10	0.031	0.043
D_1	0.80	0.90	0.031	0.035
E	1.20	1.40	0.047	0.055
F	0.08	0.18	0.003	0.007
L	0.475REF		0.019REF	
L_1	0.25	0.40	0.010	0.016
H	-	0.14	-	0.006

Suggested Pad Layout



Symbol	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
X	0.65	0.75	0.026	0.030
Y	0.65	0.75	0.026	0.030
Z	2.10	2.20	0.084	0.088